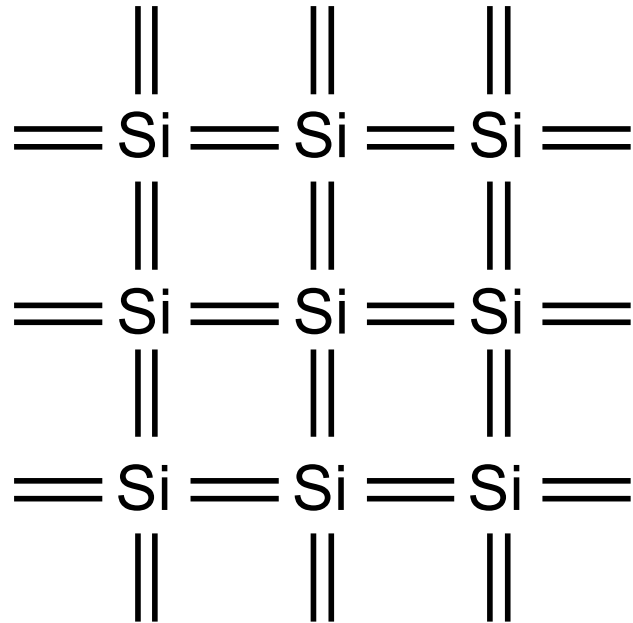


ECE1388 VLSI Design Methodology

Lecture 1: Review of CMOS Devices and Circuits

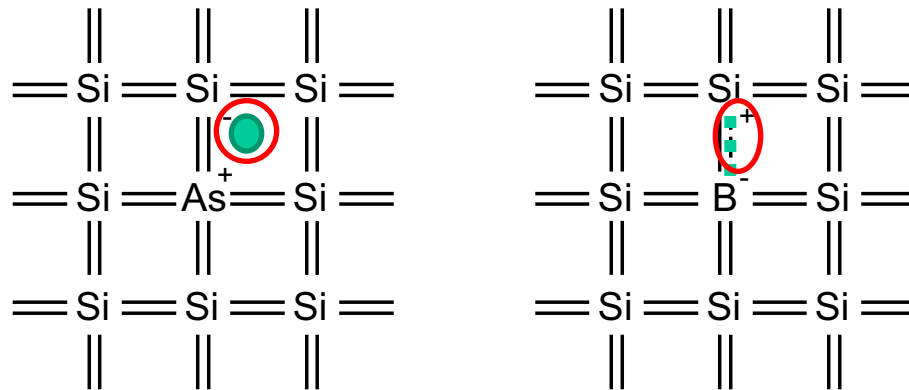
Silicon Lattice

- ❑ Transistors are built on a silicon substrate
- ❑ Silicon is a Group IV material
- ❑ Forms crystal lattice with bonds to four neighbors



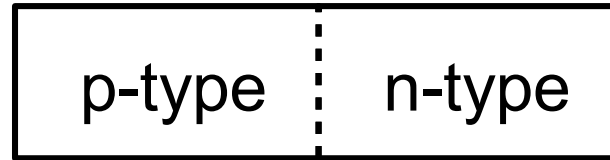
Dopants

- ❑ Silicon is a semiconductor
- ❑ Pure silicon has no free carriers and conducts poorly
- ❑ Adding dopants increases the conductivity
- ❑ Group V: extra electron (n-type, eg Arsenic)
- ❑ Group III: missing electron, called hole (p-type, eg Boron)



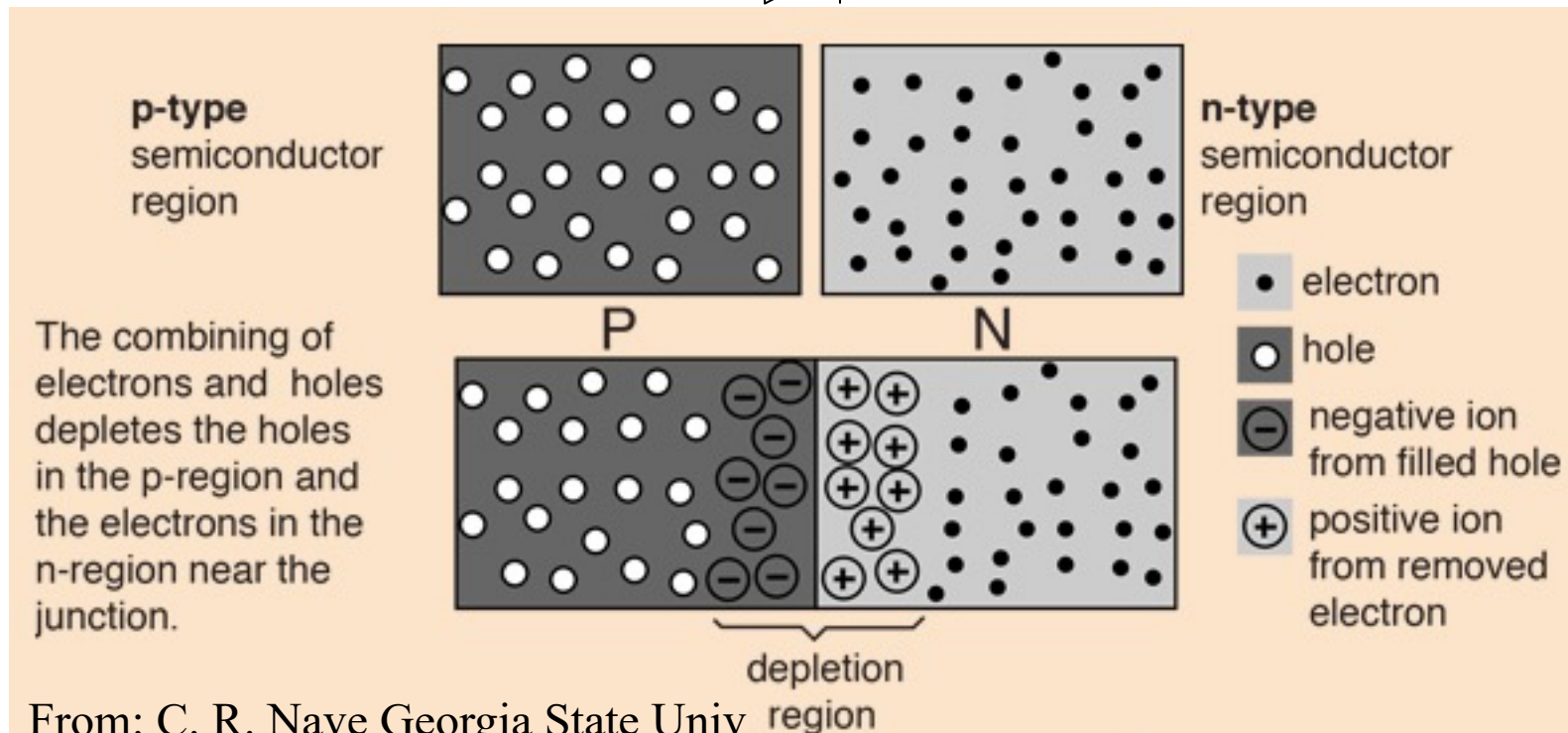
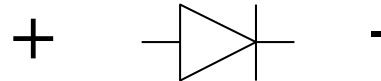
p-n Junctions

- ❑ A junction between p-type and n-type semiconductor forms a diode.



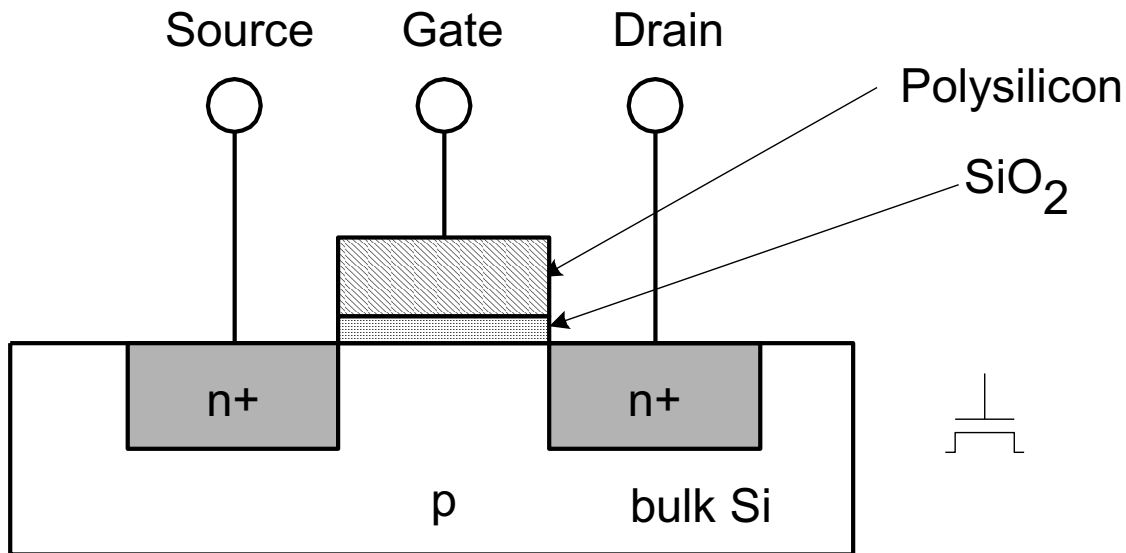
- ❑ Current flows only in one direction

anode cathode



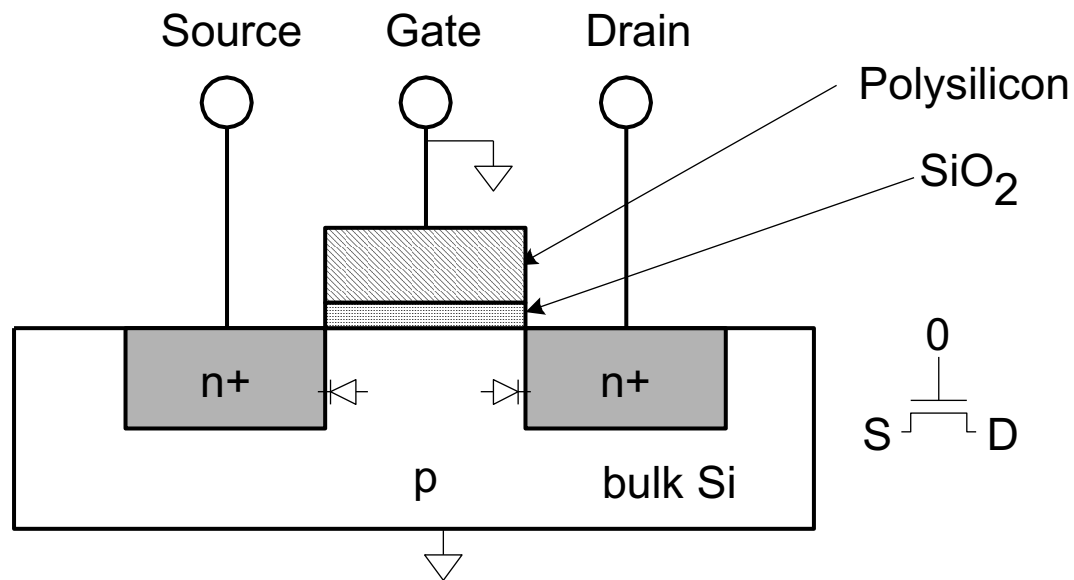
nMOS Transistor

- ❑ Four terminals: gate, source, drain, body (aka bulk)
- ❑ Gate – oxide – body stack looks like a **capacitor**
 - Gate and body are conductors
 - SiO_2 (oxide) is a very good insulator
 - Called metal – oxide – semiconductor (MOS) capacitor
 - Even though gate is no longer made of metal



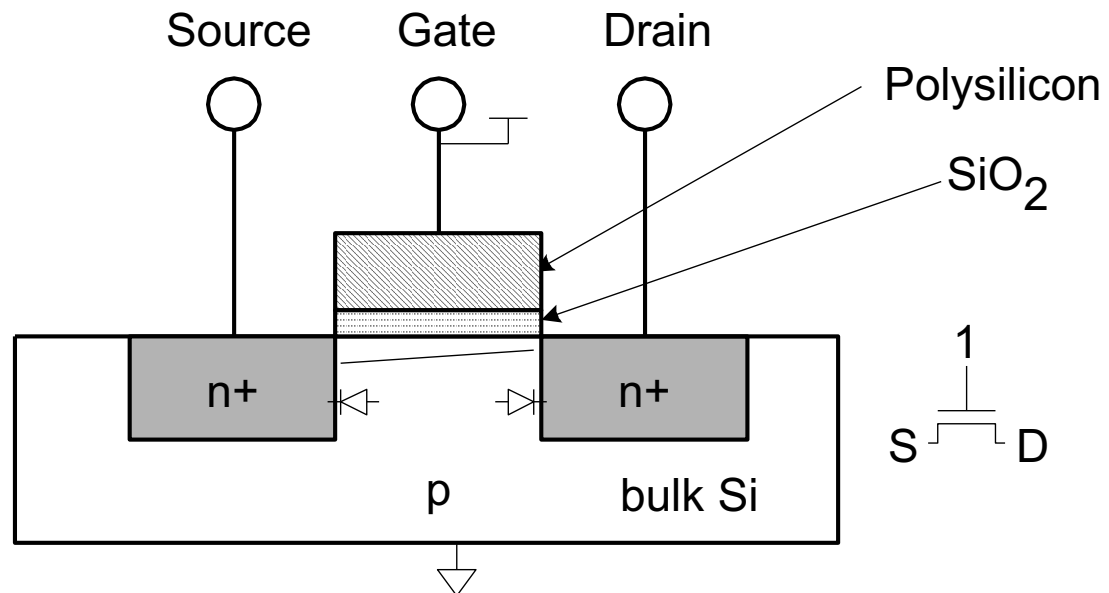
nMOS Operation

- ❑ Body is commonly tied to ground (0 V)
- ❑ When the gate is at a low voltage:
 - P-type body is at low voltage, there is no 'channel'
 - Source-body and drain-body diodes are OFF
 - No current flows, transistor is OFF



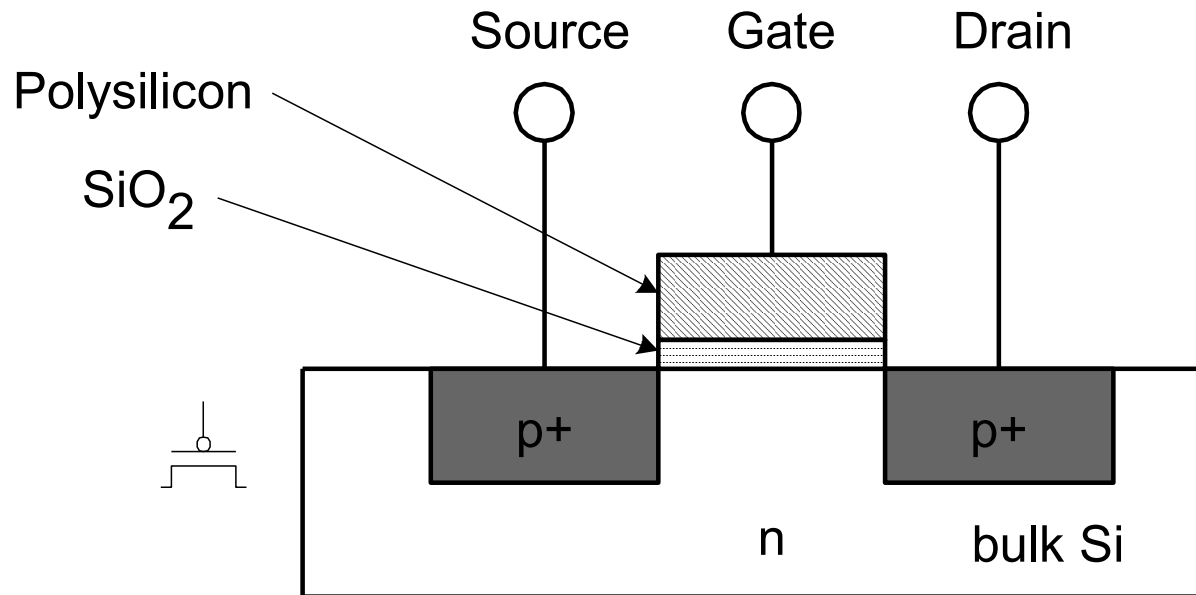
nMOS Operation Cont.

- When the gate is at a high voltage:
 - Positive charge on gate of MOS capacitor
 - Negative charge attracted to body
 - Inverts a channel under gate to n-type
 - Now current can flow through n-type silicon from source through channel to drain, transistor is ON

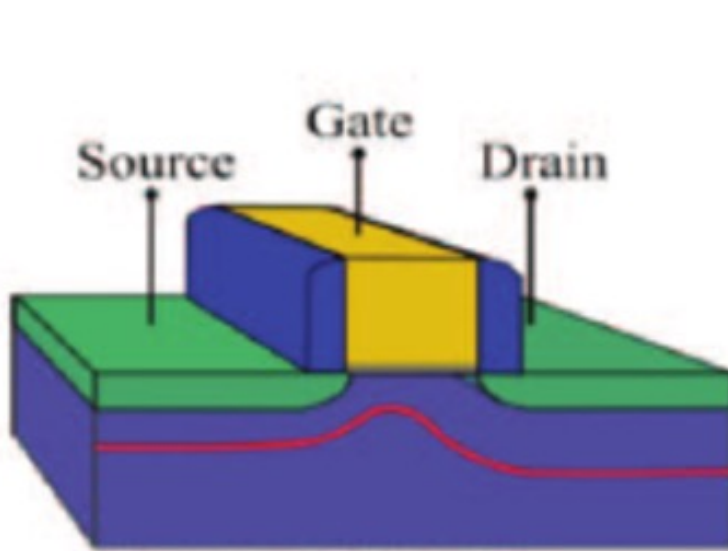


pMOS Transistor

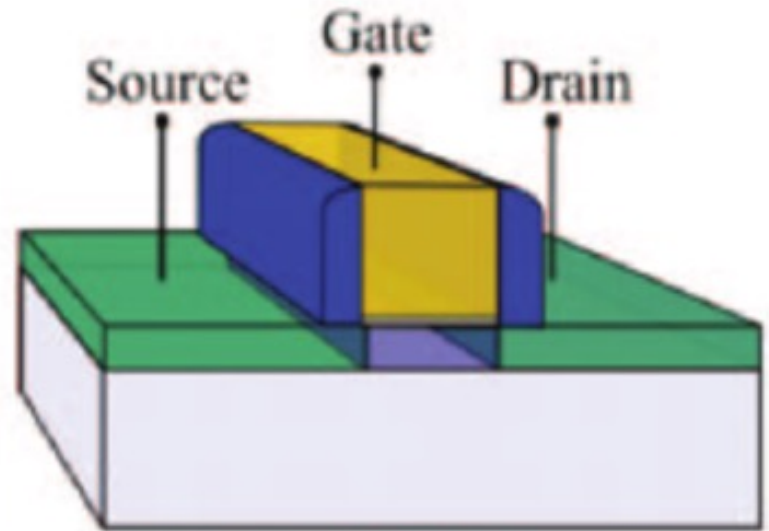
- ❑ Similar, but doping and voltages reversed
 - Body tied to high voltage (V_{DD})
 - Gate low: transistor ON
 - Gate high: transistor OFF
 - Bubble indicates inverted behavior



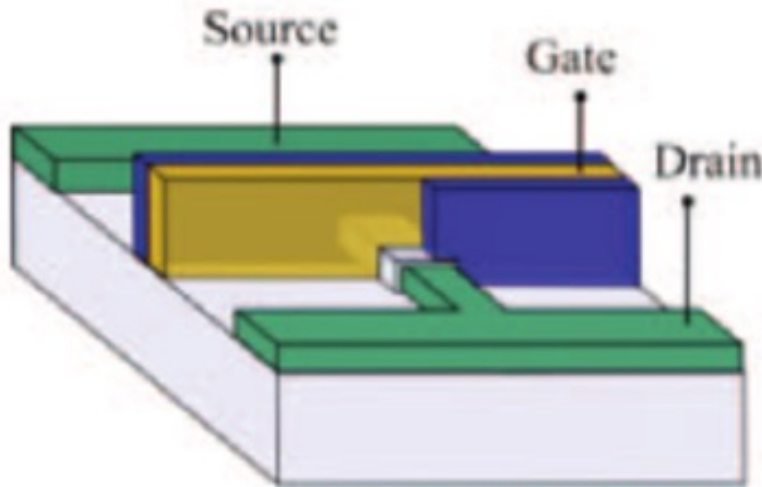
Modern Transistors



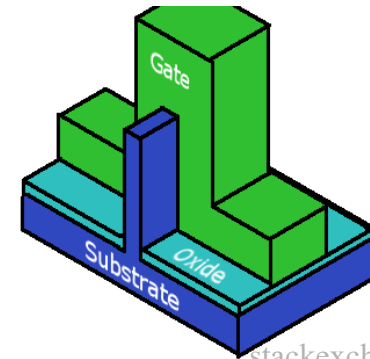
Bulk MOSFET (planar MOSFET)



UTB-SOI MOSFET
(ultra-thin body silicon-on-insulator MOSFET)



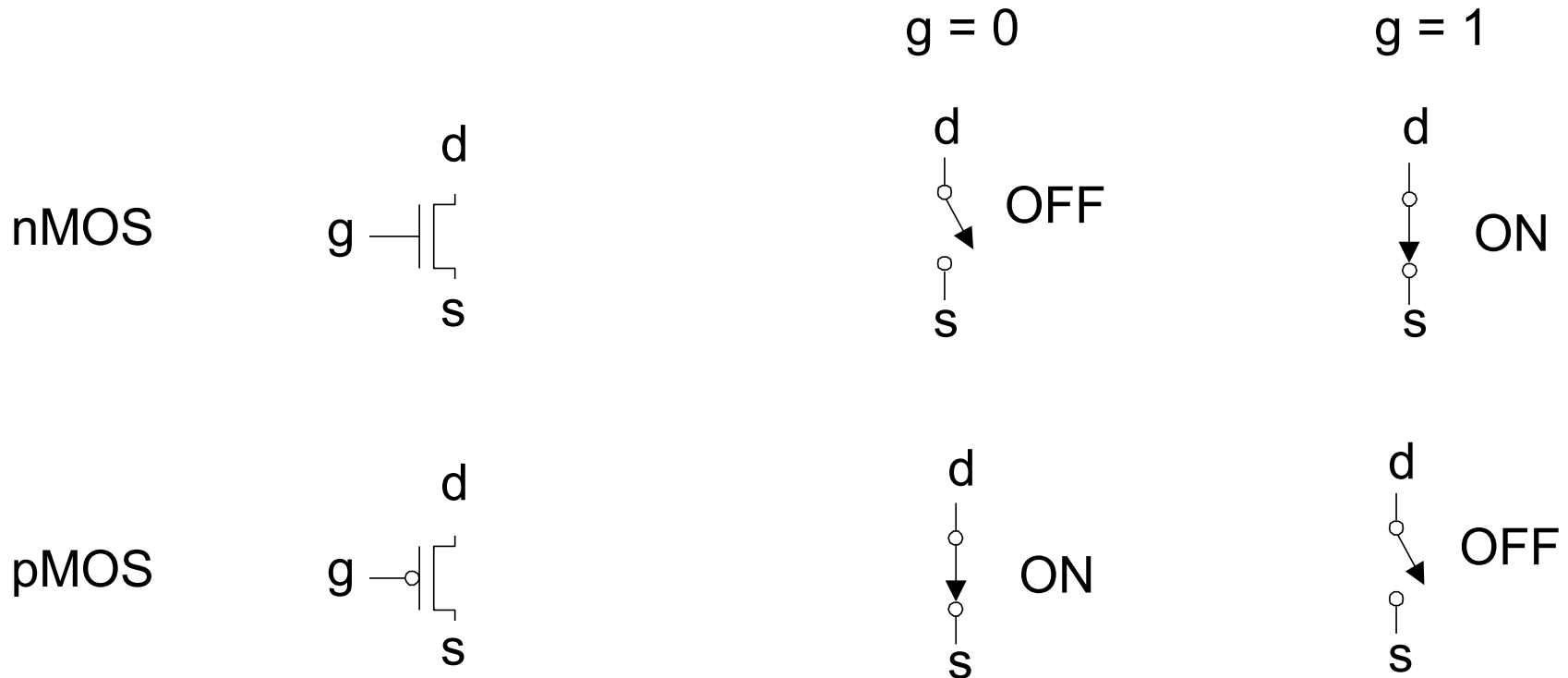
FinFet (Tri-gate MOSFET) on SOI



FinFet (Tri-gate MOSFET) on bulk

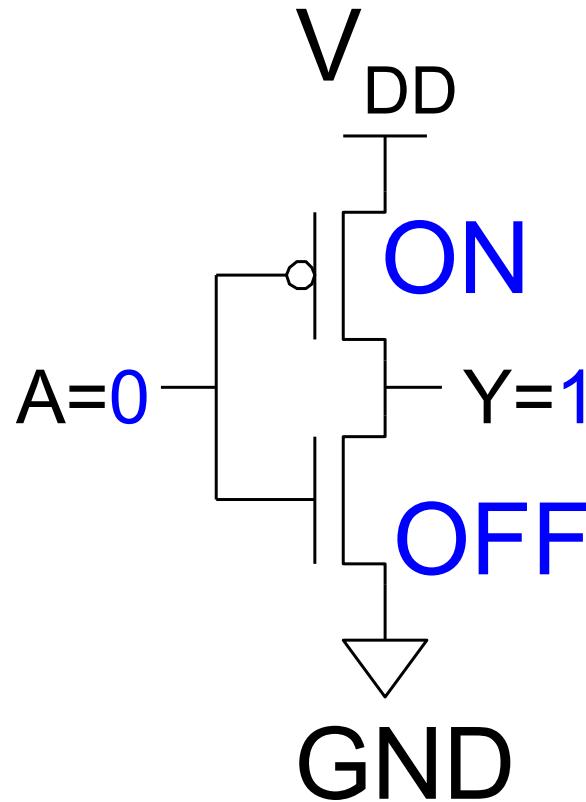
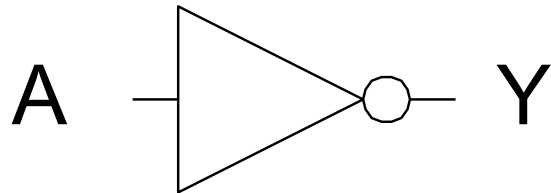
Transistors as Switches

- ❑ We can view MOS transistors as electrically controlled switches
- ❑ Voltage at gate controls path from source to drain



Static CMOS Logic: Inverter

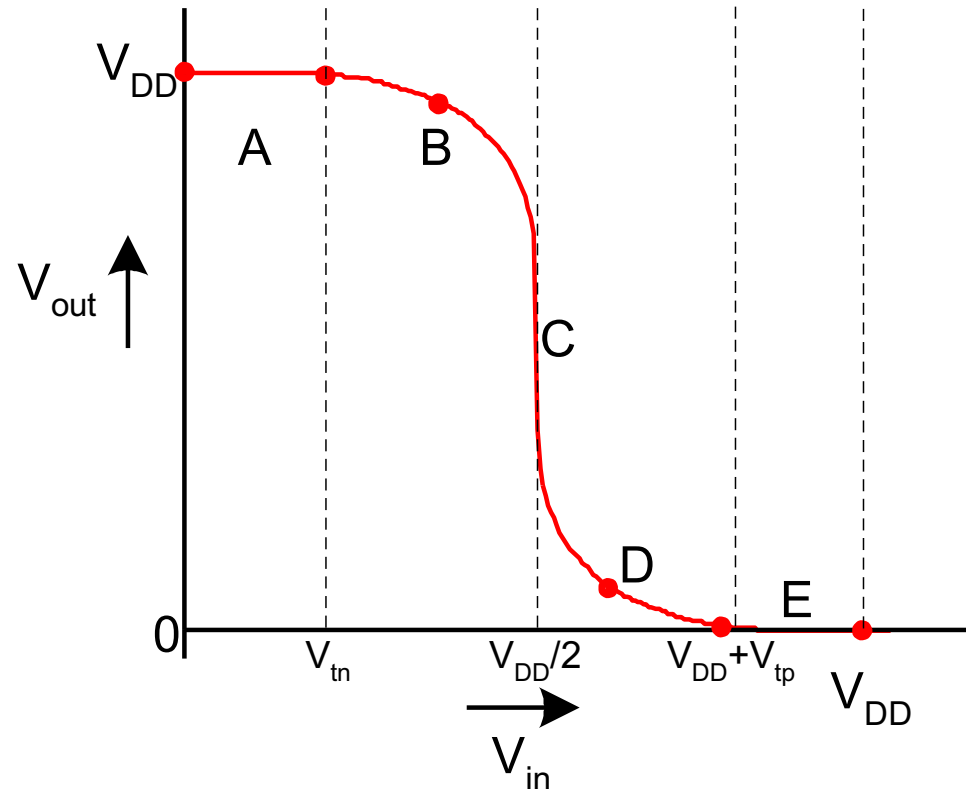
A	Y
0	1
1	0



Signal Level Restoring

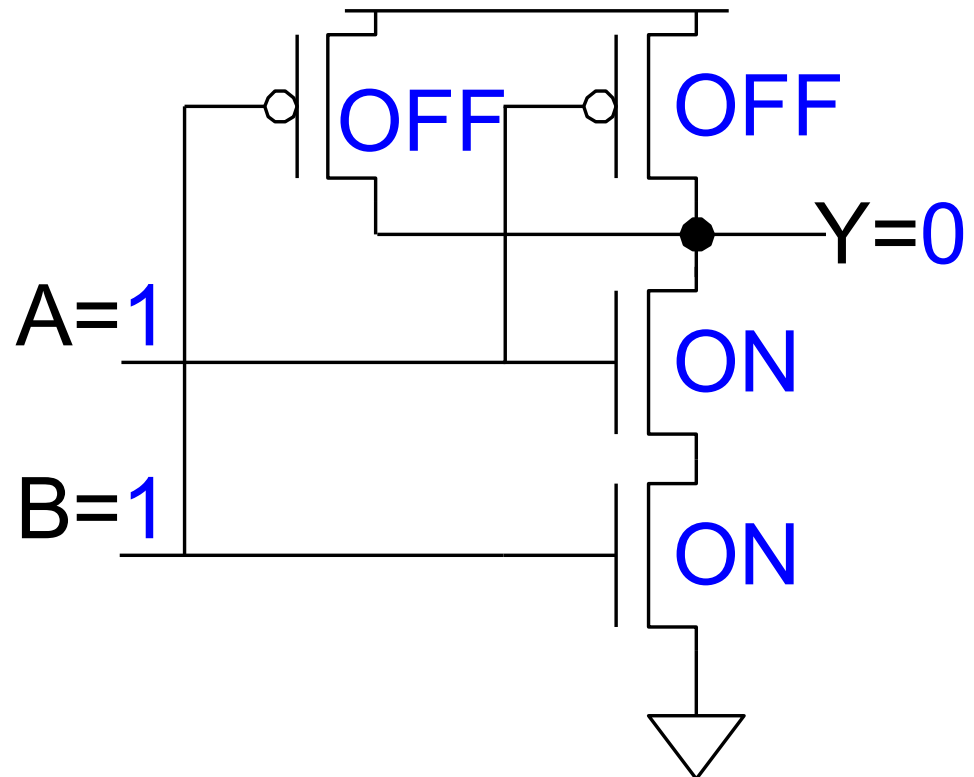
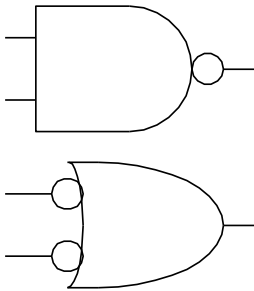
- ❑ Static CMOS logic: Inherently signal level-restoring

Region	nMOS	pMOS
A	Cutoff	Linear
B	Saturation	Linear
C	Saturation	Saturation
D	Linear	Saturation
E	Linear	Cutoff



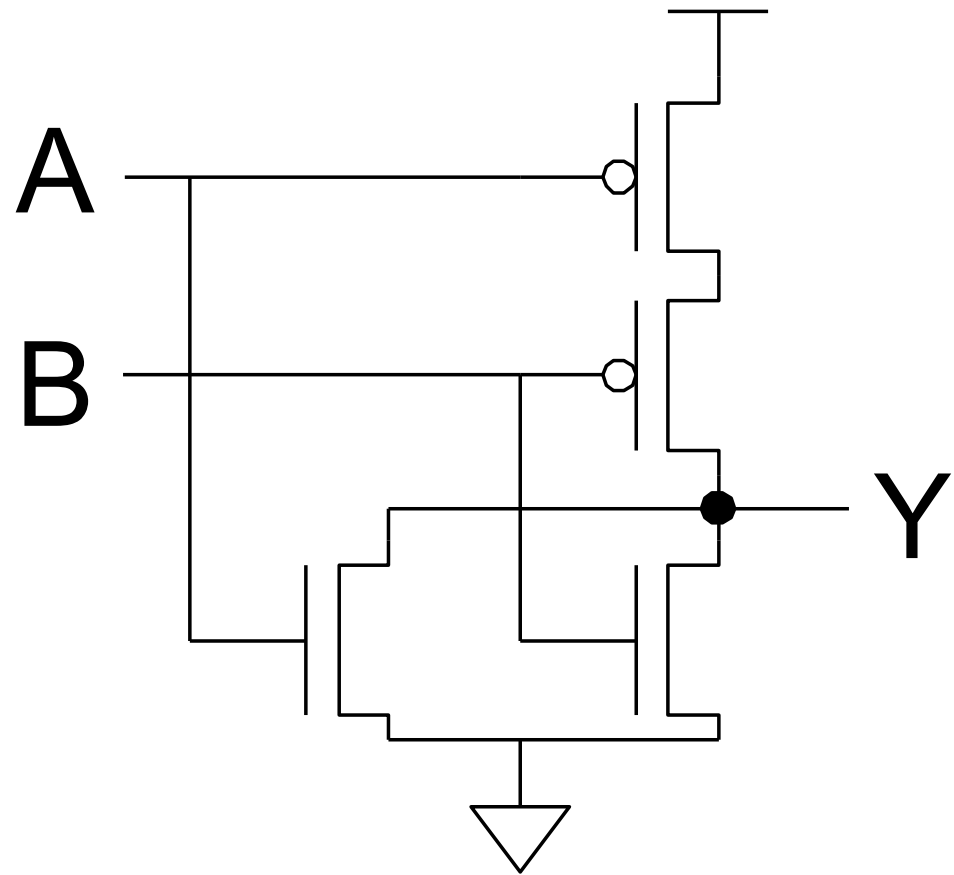
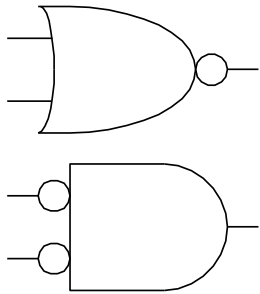
CMOS NAND Gate

A	B	Y
0	0	1
0	1	1
1	0	1
1	1	0



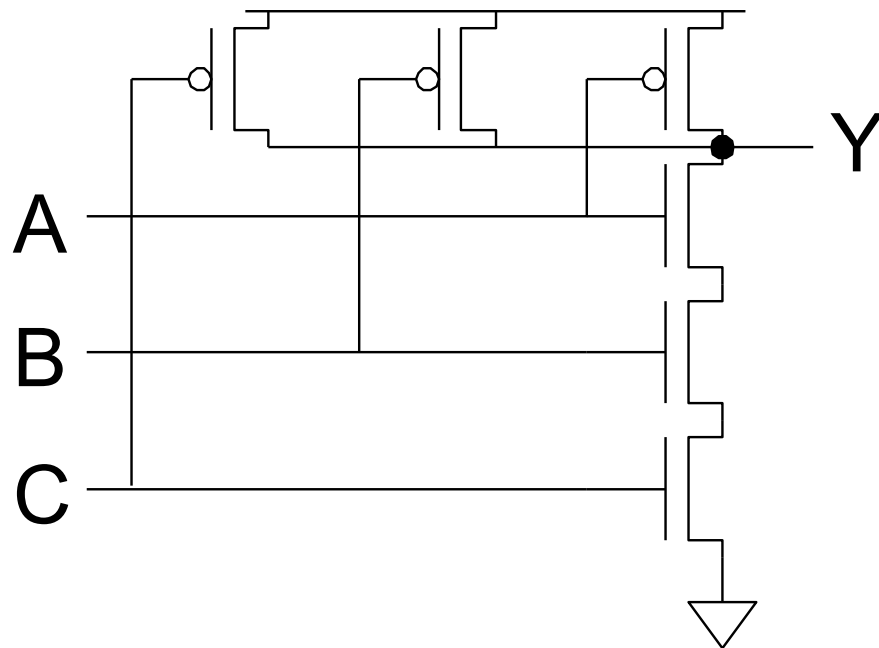
CMOS NOR Gate

A	B	Y
0	0	1
0	1	0
1	0	0
1	1	0



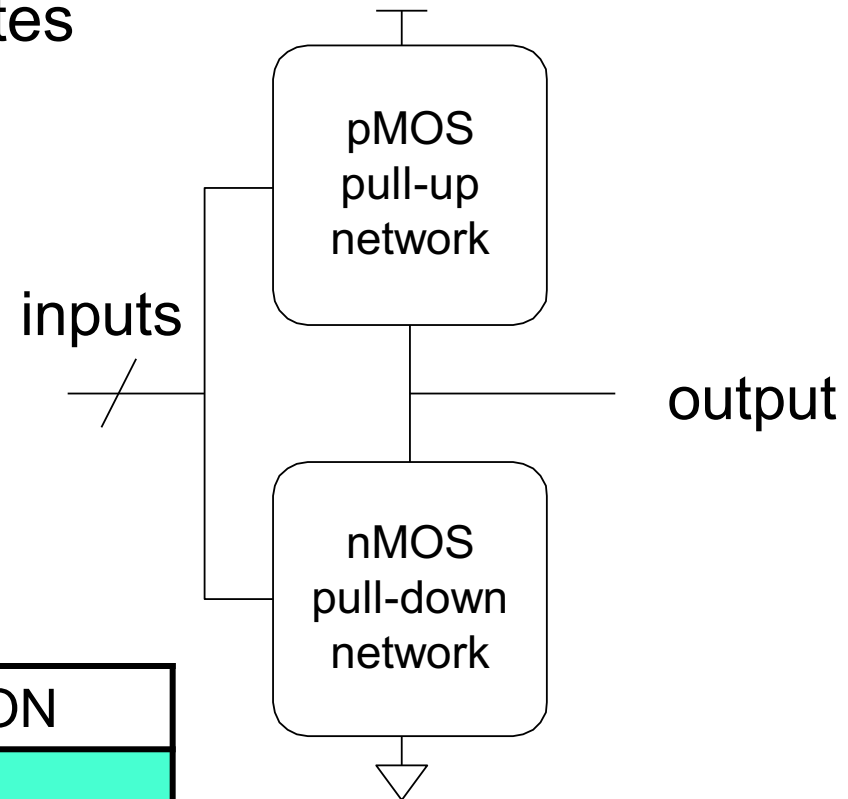
3-input NAND Gate

- ❑ Y pulls low if ALL inputs are 1
- ❑ Y pulls high if ANY input is 0



Complementary CMOS

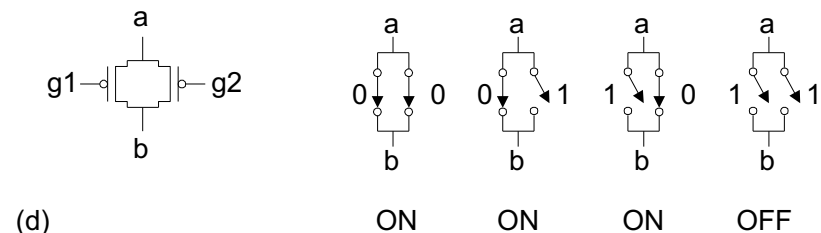
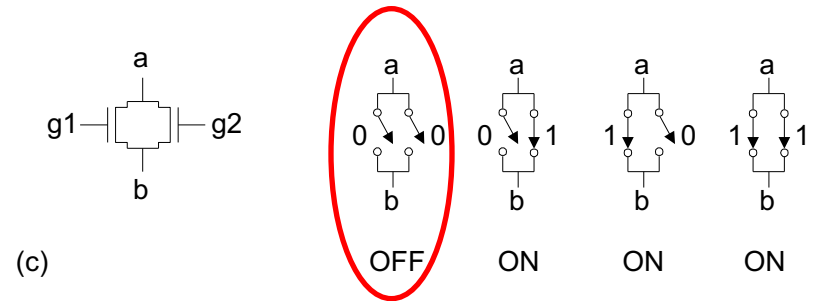
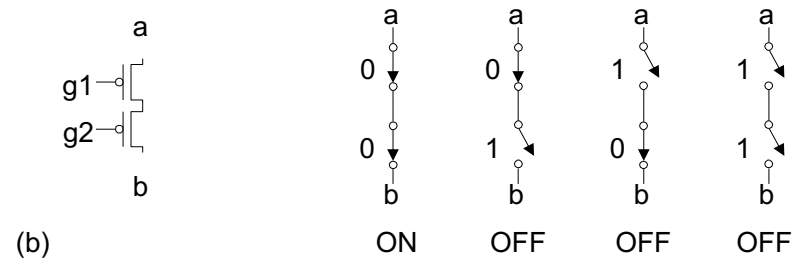
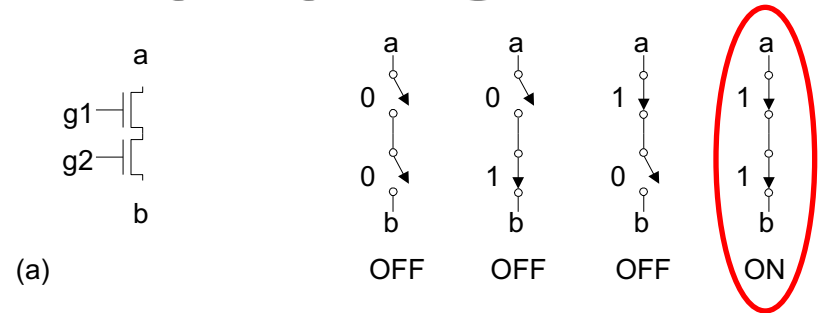
- ❑ Complementary CMOS logic gates
 - nMOS *pull-down network*
 - pMOS *pull-up network*
 - a.k.a. static CMOS



	Pull-up OFF	Pull-up ON
Pull-down OFF	Z (floating – in some cases)	1
Pull-down ON	0	X (crowbar - never)

Series and Parallel

- ❑ nMOS: 1 = ON
- ❑ pMOS: 0 = ON
- ❑ *Series*: both must be ON



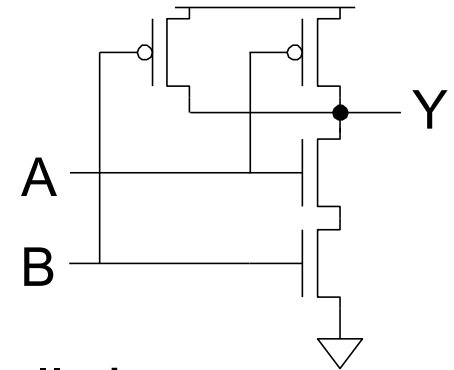
- ❑ *Parallel*: either can be ON

Conduction Complement

- ❑ Complementary CMOS gates always produce 0 or 1

- ❑ Ex: NAND gate

- Series nMOS: $Y=0$ when both inputs are 1
- Thus $Y=1$ when either input is 0
- Requires parallel pMOS

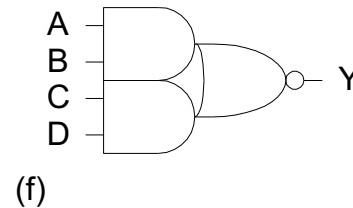
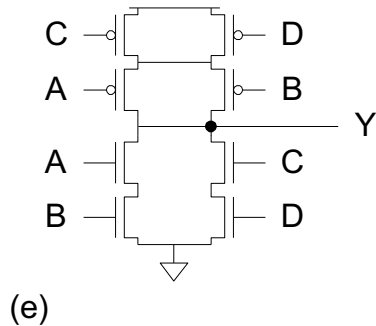
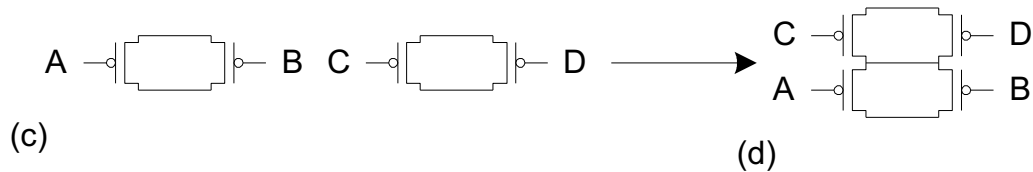


- ❑ Rule of *Conduction Complements*

- Pull-up network is complement of pull-down
- Parallel \rightarrow series, series \rightarrow parallel

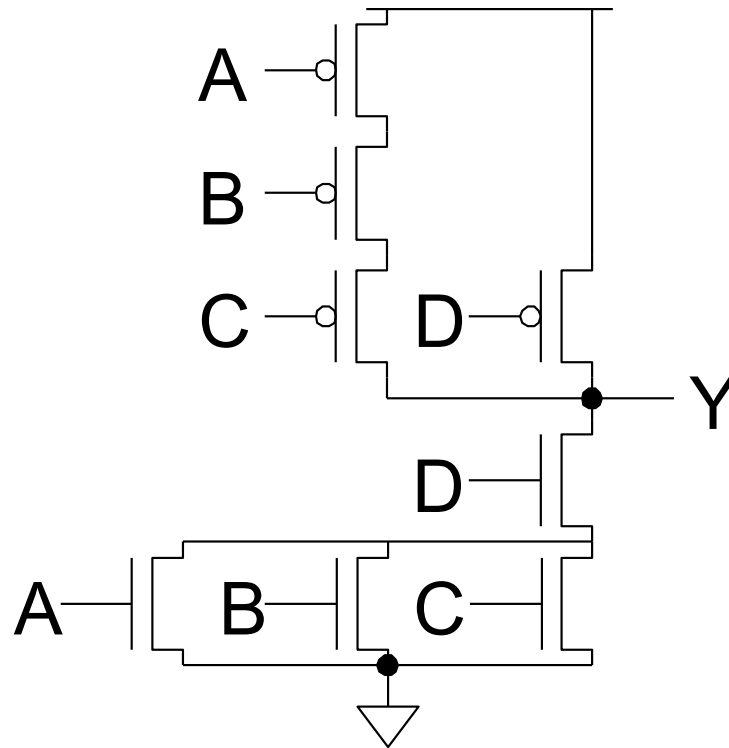
Compound Gates

- ❑ Compound gates can do any inverting function
- ❑ Ex: $Y = A \cdot B + C \cdot D$ (AND-AND-OR-INVERT, AOI22)



Example: O3AI

$$\square \quad Y = \overline{(A + B + C)} \cdot D$$

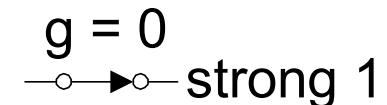
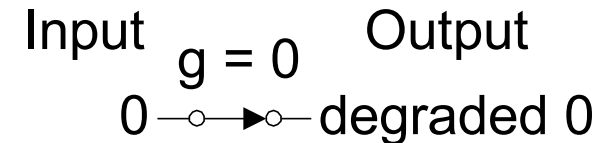
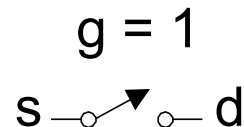
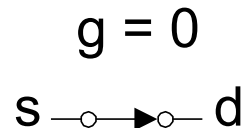
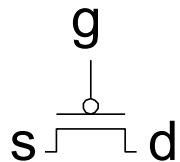
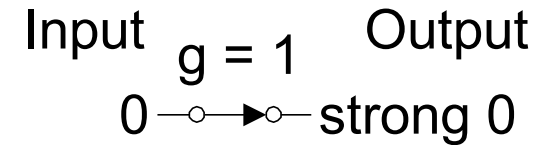
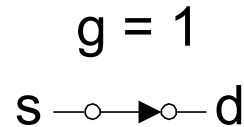
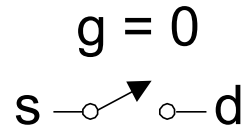
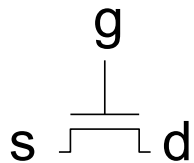


Signal Strength

- ❑ *Strength* of signal
 - How close it approximates ideal voltage source
- ❑ V_{DD} and GND rails are strongest 1 and 0
- ❑ nMOS pass strong 0
 - But degraded or weak 1
- ❑ pMOS pass strong 1
 - But degraded or weak 0
- ❑ Thus:
 - **nMOS** are best for **pull-down** network
 - **pMOS** are best for **pull-up** network

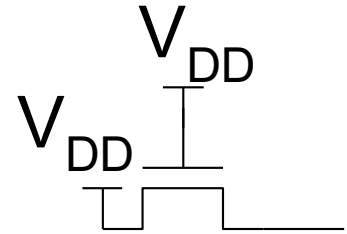
Pass Transistors

□ Transistors can be used as switches



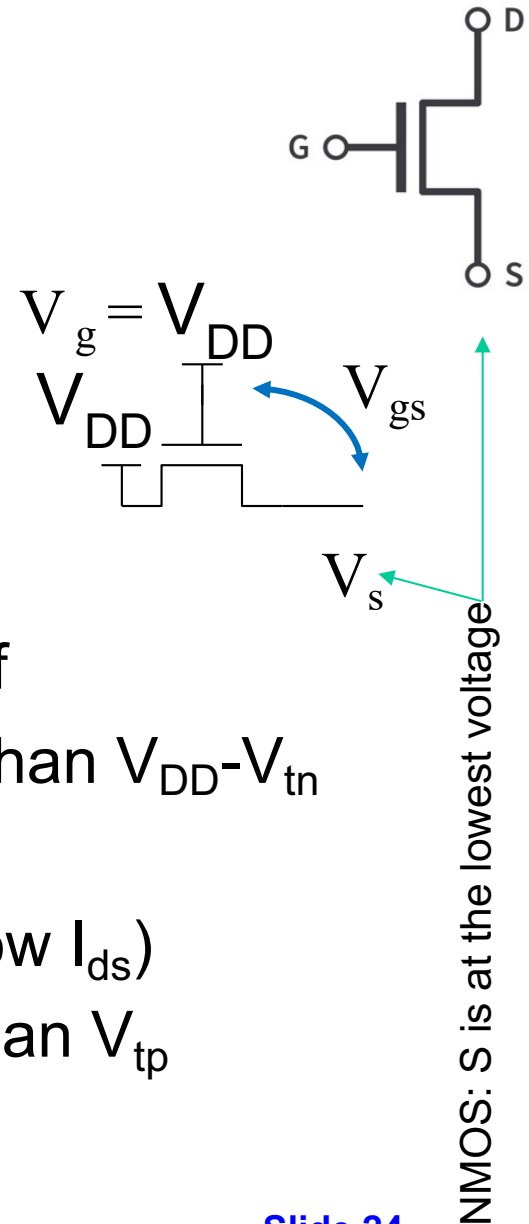
Pass Transistors: Degraded Signals

- ❑ We have assumed source is grounded
- ❑ What if source > 0 ?
 - e.g. pass transistor passing V_{DD}

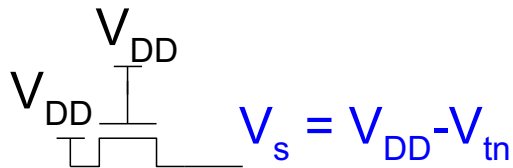


Pass Transistors: Degraded Signals

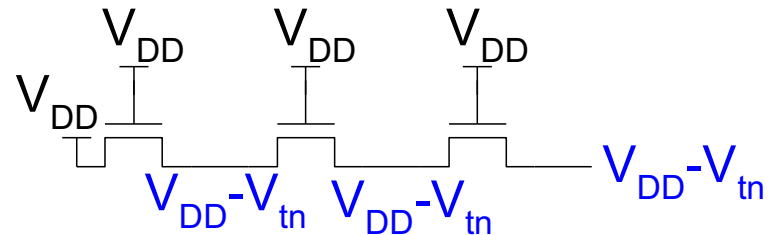
- ❑ We have assumed source is grounded
- ❑ What if source > 0 ?
 - e.g. pass transistor passing V_{DD}
- ❑ $V_g = V_{DD}$
 - If $V_s > V_{DD} - V_t$, $V_{gs} < V_t$
 - Hence transistor would turn itself off
- ❑ nMOS pass transistors pull no higher than $V_{DD} - V_{tn}$
 - Called a degraded “1”
 - Approach degraded value slowly (low I_{ds})
- ❑ pMOS pass transistors pull no lower than V_{tp}



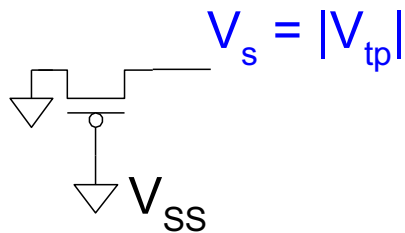
Pass Transistor Ckts



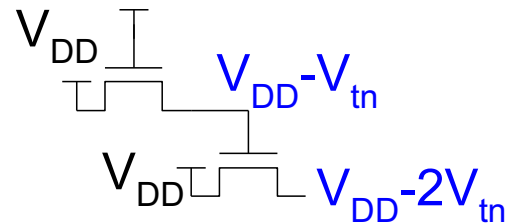
✗ Degraded “1”



✗ Very slow



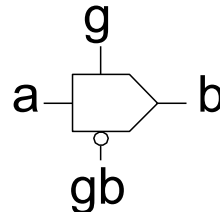
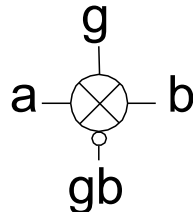
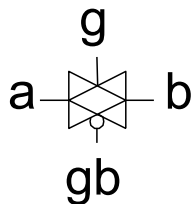
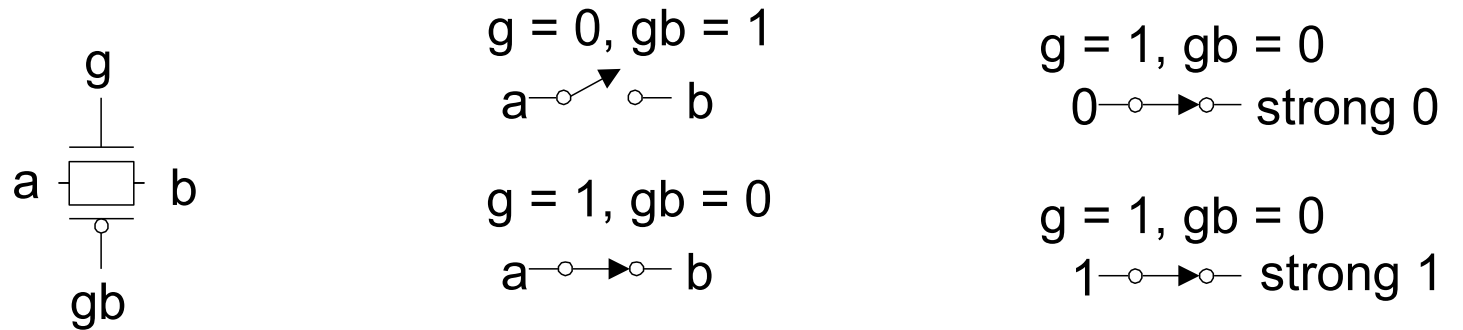
✗ Degraded “0”



✗ Very slow

Transmission Gates

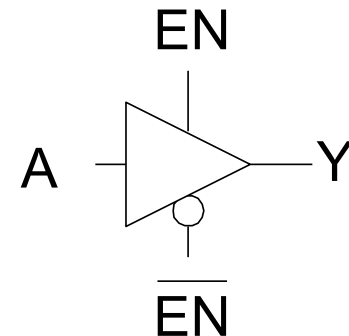
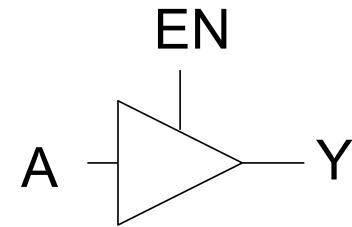
- ❑ Pass transistors produce degraded outputs
- ❑ *Transmission gates* pass both 0 and 1 well



Tristates

- ❑ *Tristate buffer* produces Z when not enabled

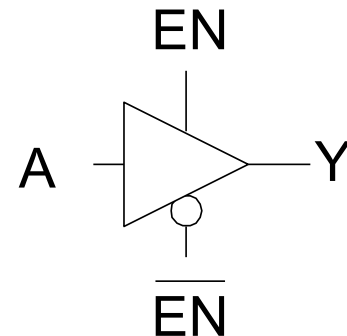
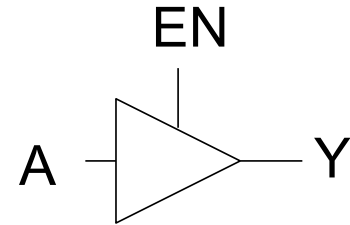
EN	A	Y
0	0	
0	1	
1	0	
1	1	



Tristates

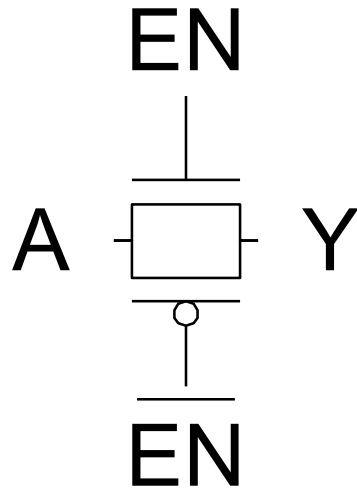
- ❑ *Tristate buffer* produces Z when not enabled

EN	A	Y
0	0	Z
0	1	Z
1	0	0
1	1	1



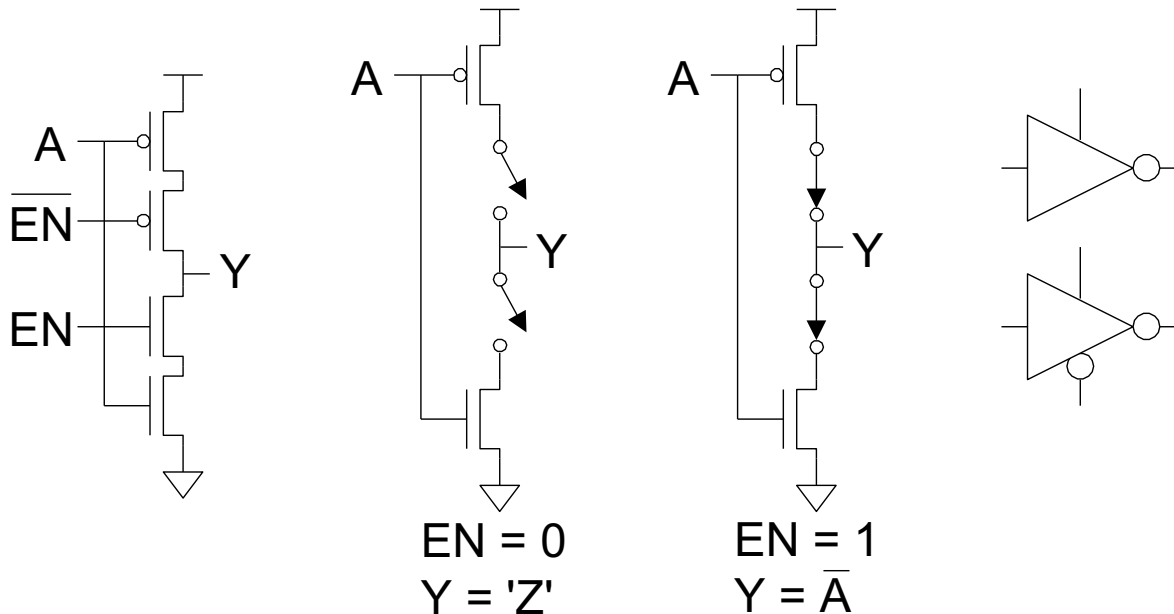
Nonrestoring Tristate

- ❑ Transmission gate acts as tristate buffer
 - Only two transistors
 - But *nonrestoring*
 - Noise on A is passed on to Y



Restoring Tristate Inverter

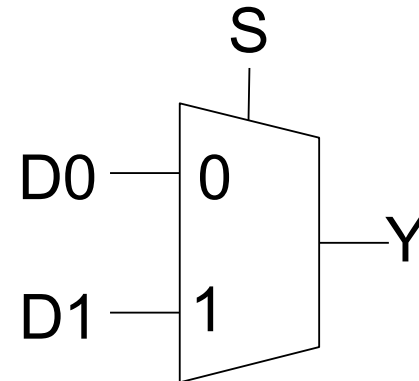
- ❑ Tristate inverter produces restored output
 - Violates conduction complement rule
 - Because we want a Z output



Multiplexers

- ❑ 2:1 *multiplexer* chooses between two inputs

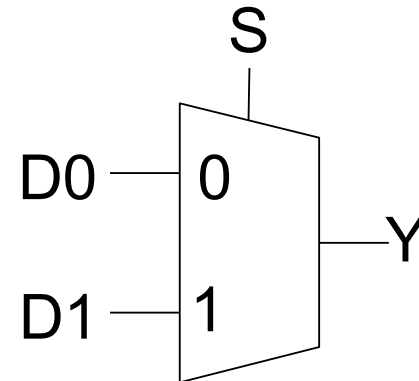
S	D1	D0	Y
0	X	0	
0	X	1	
1	0	X	
1	1	X	



Multiplexers

- ❑ 2:1 multiplexer chooses between two inputs

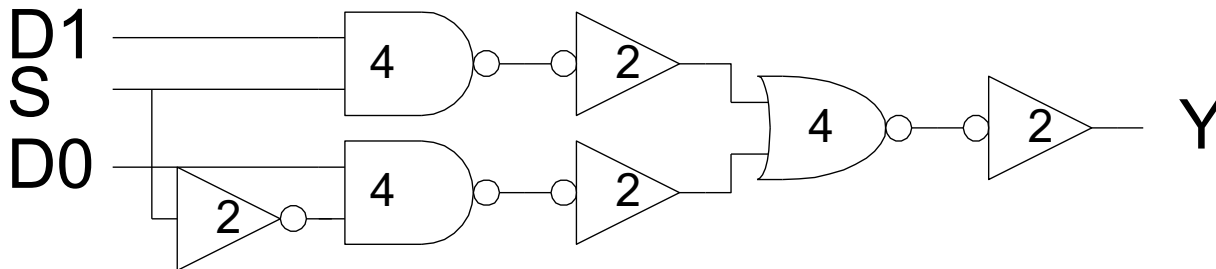
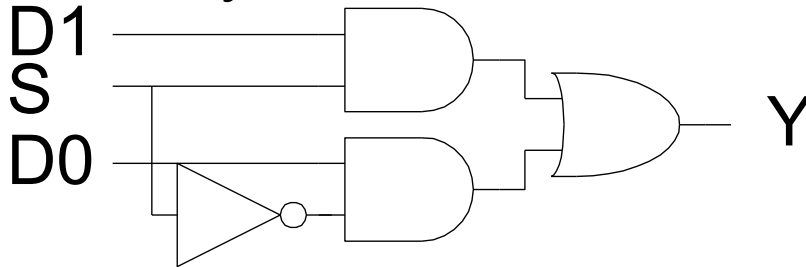
S	D1	D0	Y
0	X	0	0
0	X	1	1
1	0	X	0
1	1	X	1



Gate-Level Mux Design

❑ $Y = SD_1 + \bar{S}D_0$ (too many transistors)

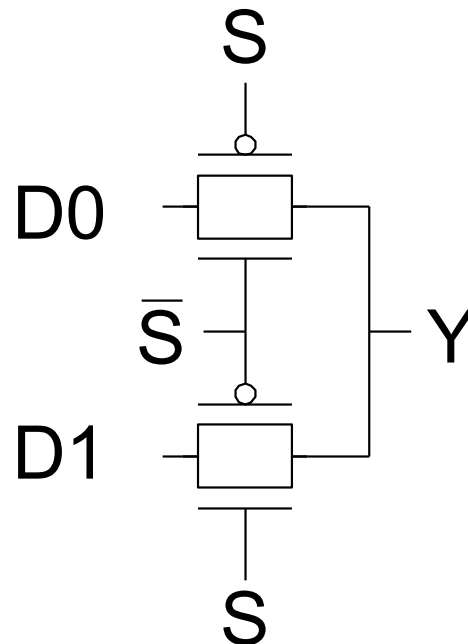
❑ How many transistors are needed? 20



❑ Can be further optimized to 14 transistors (the last three stages can be replaced by a NAND gate)

Transmission Gate Mux

- ❑ Nonrestoring mux uses two transmission gates
 - Only 4 transistors

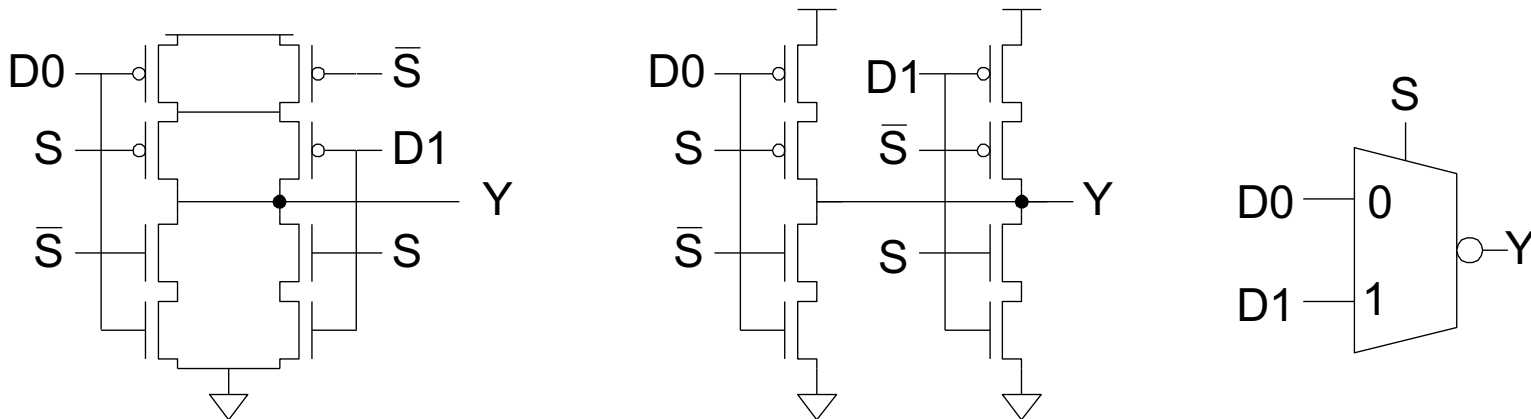


Restoring Inverting Mux

❑ Inverting multiplexer

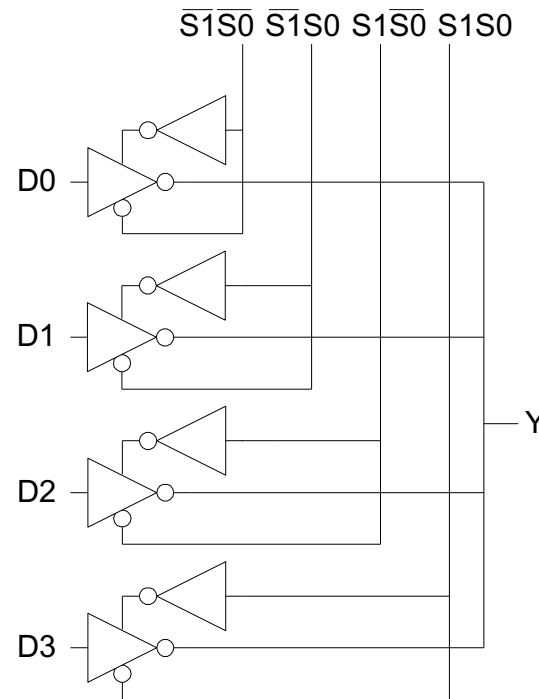
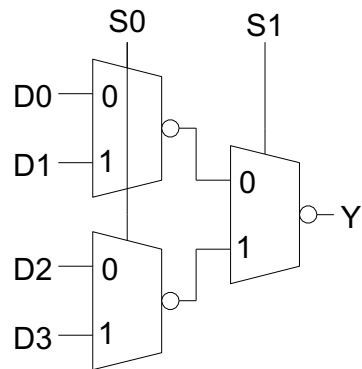
- Use compound gate (by inverting $Y = SD_1 + \bar{S}D_0$)
- Or a pair of tristate inverters
- Essentially the same thing

❑ Noninverting multiplexer adds an inverter



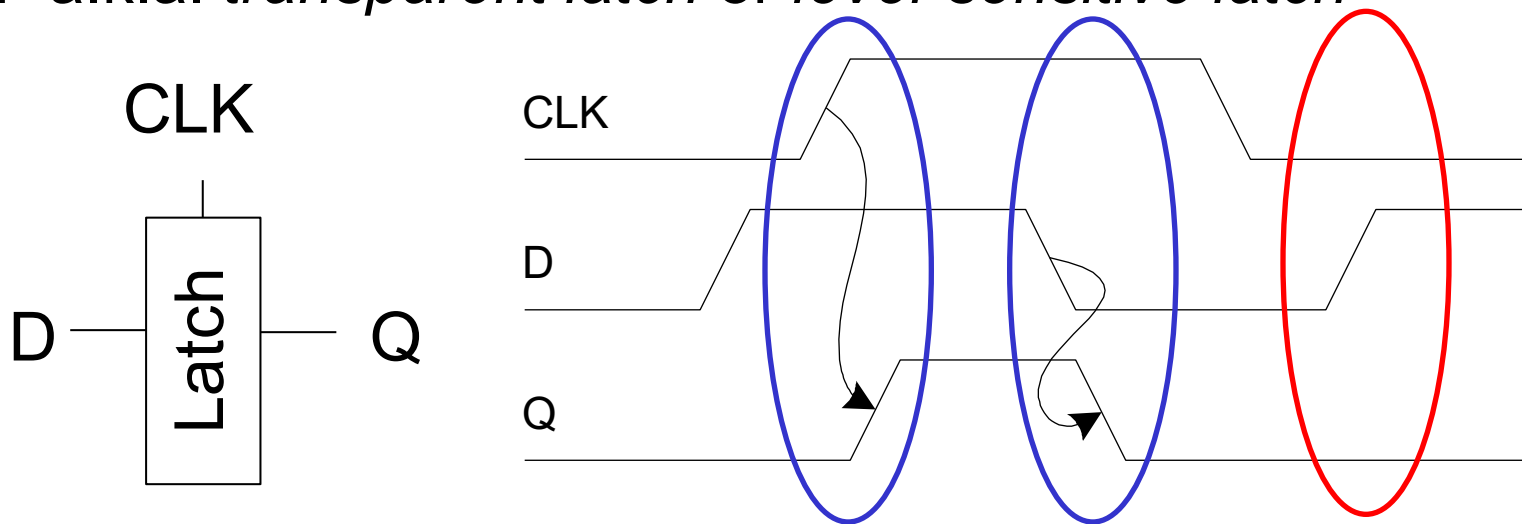
4:1 Multiplexer

- ❑ 4:1 mux chooses one of 4 inputs using two selects
 - Two levels of 2:1 muxes
 - Or four tristates



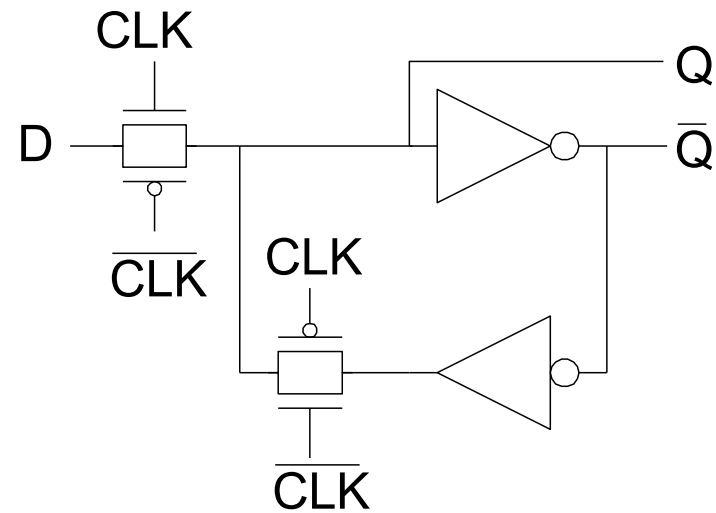
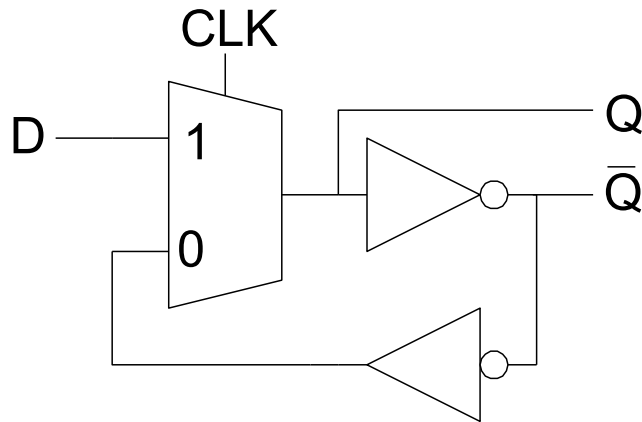
D Latch

- ❑ When $CLK = 1$, latch is *transparent*
 - D flows through to Q like a buffer
- ❑ When $CLK = 0$, the latch is *opaque*
 - Q holds its old value independent of D
- ❑ a.k.a. *transparent latch* or *level-sensitive latch*



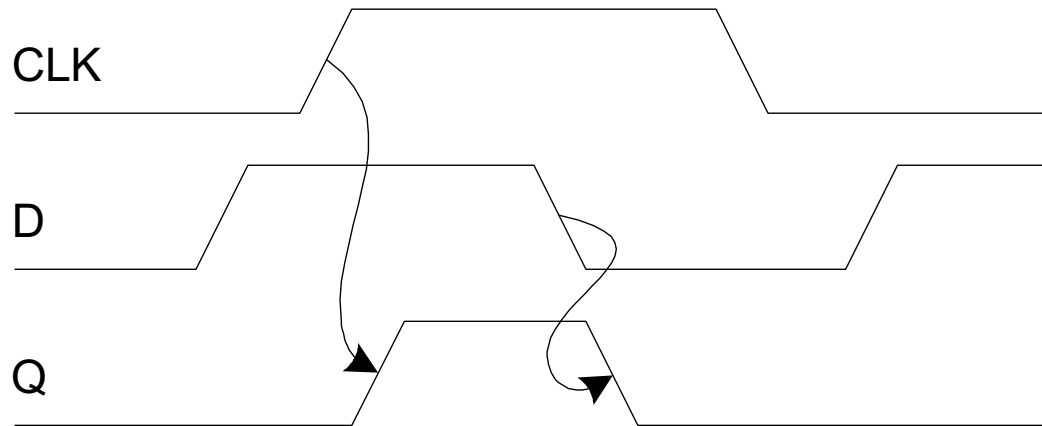
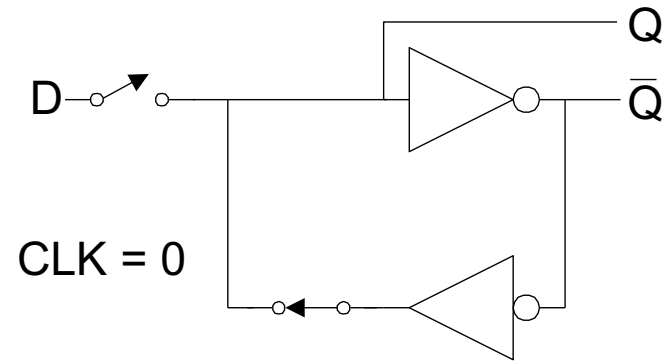
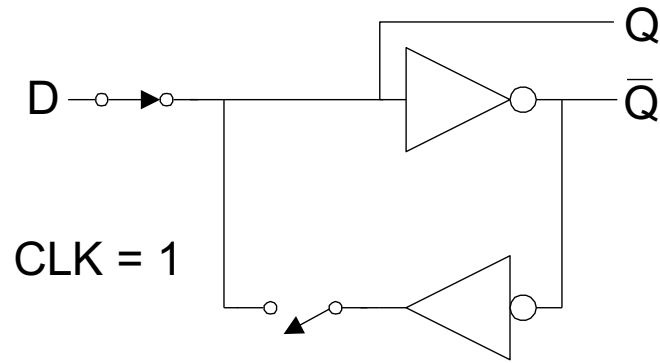
D Latch Design

- ❑ Multiplexer chooses D or old Q



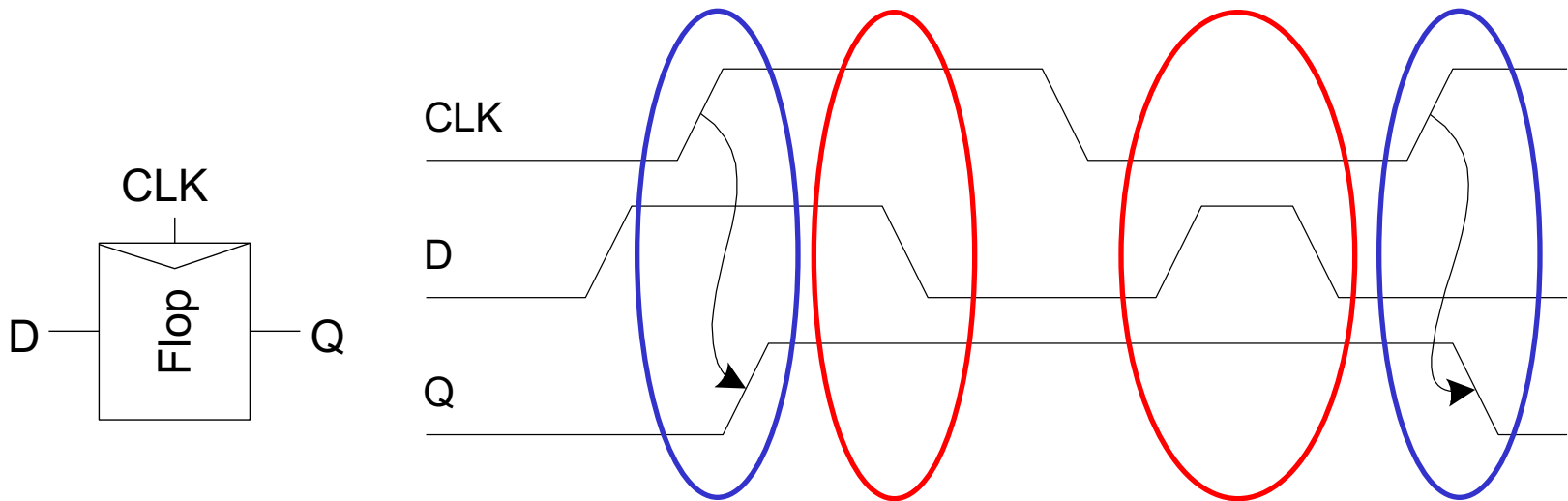
- ❑ Design hints – to avoid **common beginner's mistakes**:
 - always buffer latch outputs (e.g., in a shift register)
 - always account for (i.e., simulate) the parasitics (e.g., C and R) of wires coming to/from a latch (or a shift register)

D Latch Operation



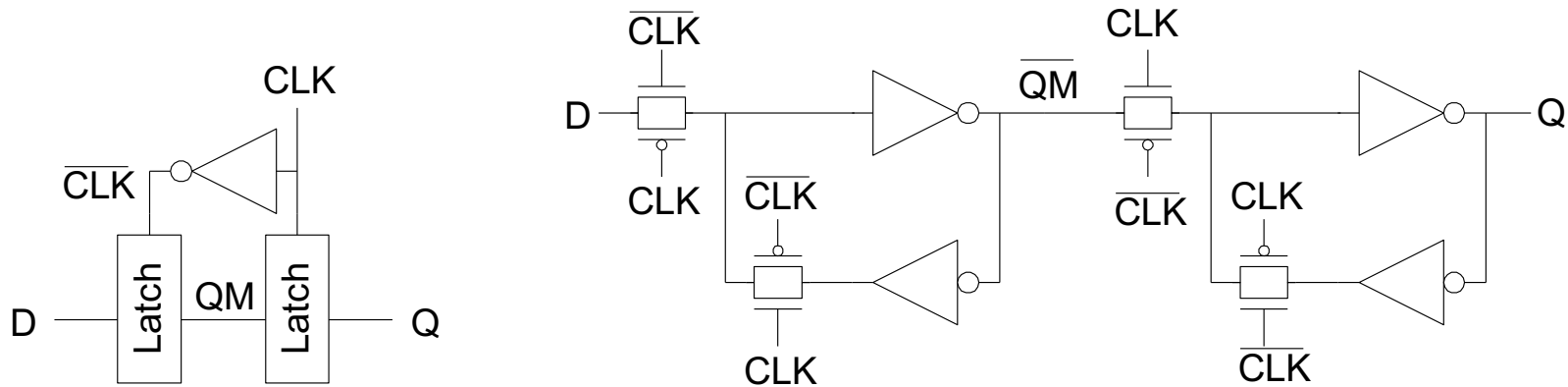
D Flip-flop

- ❑ When CLK rises, D is copied to Q
- ❑ At all other times, Q holds its value
- ❑ a.k.a. *positive edge-triggered flip-flop, master-slave flip-flop*

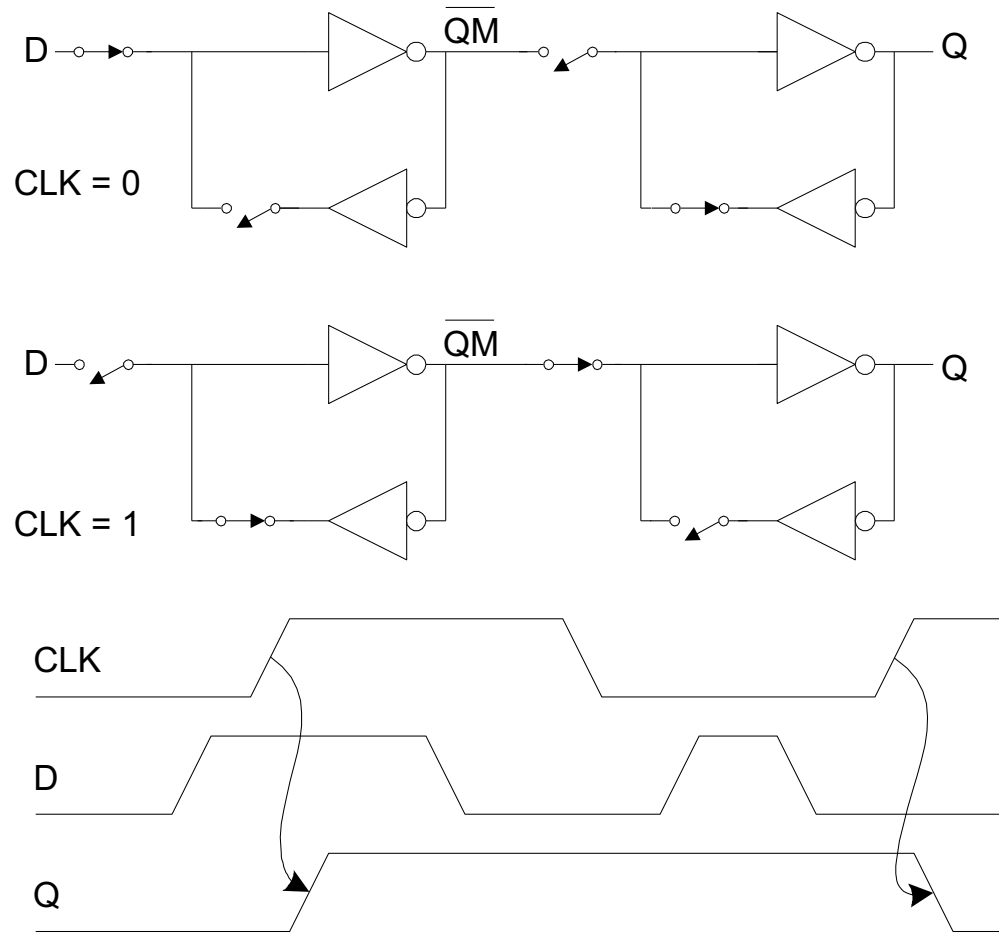


D Flip-flop Design

- ❑ Built from D latches (master and slave)



D Flip-flop Operation



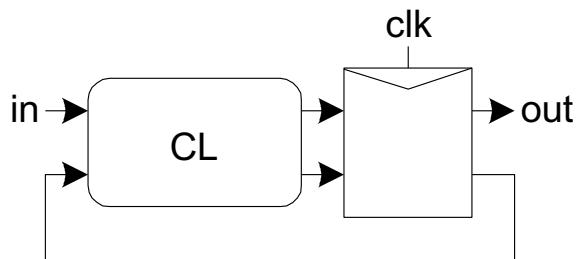
Sequencing

❑ *Combinational logic*

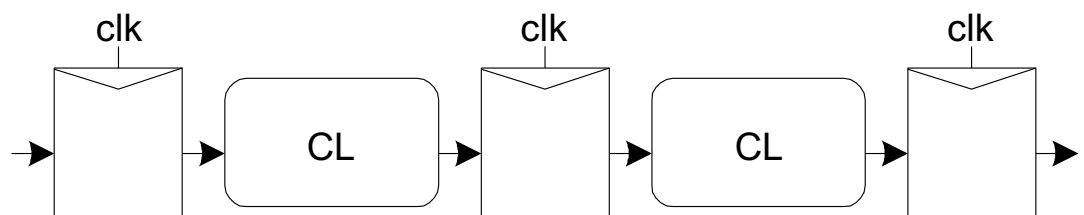
- output depends on current inputs

❑ *Sequential logic*

- uses flip-flops or latches
- output depends on current and previous inputs
- requires separating previous, current, future
- called *state* or *tokens*
- Ex: FSM, pipeline

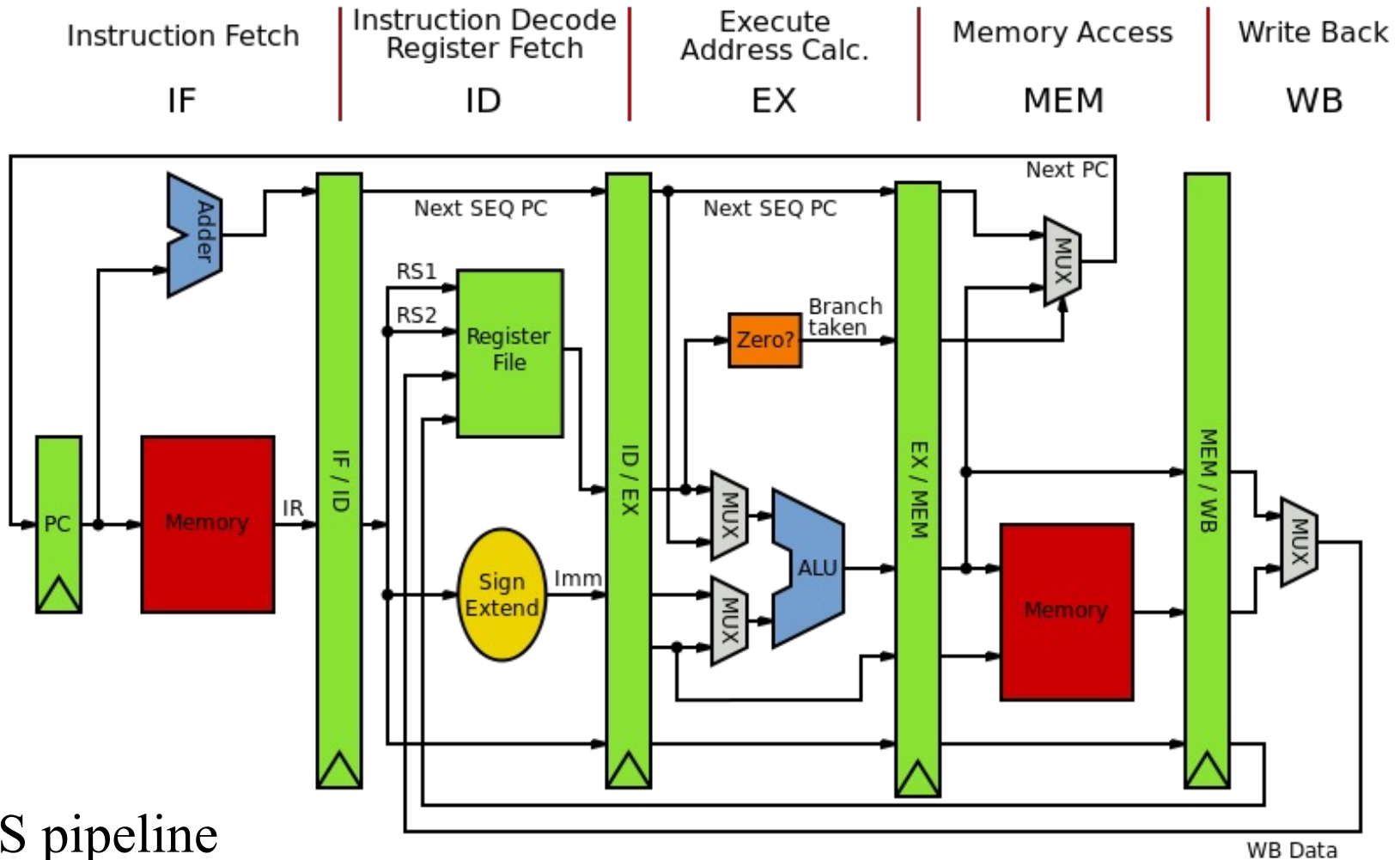


Finite State Machine



Pipeline

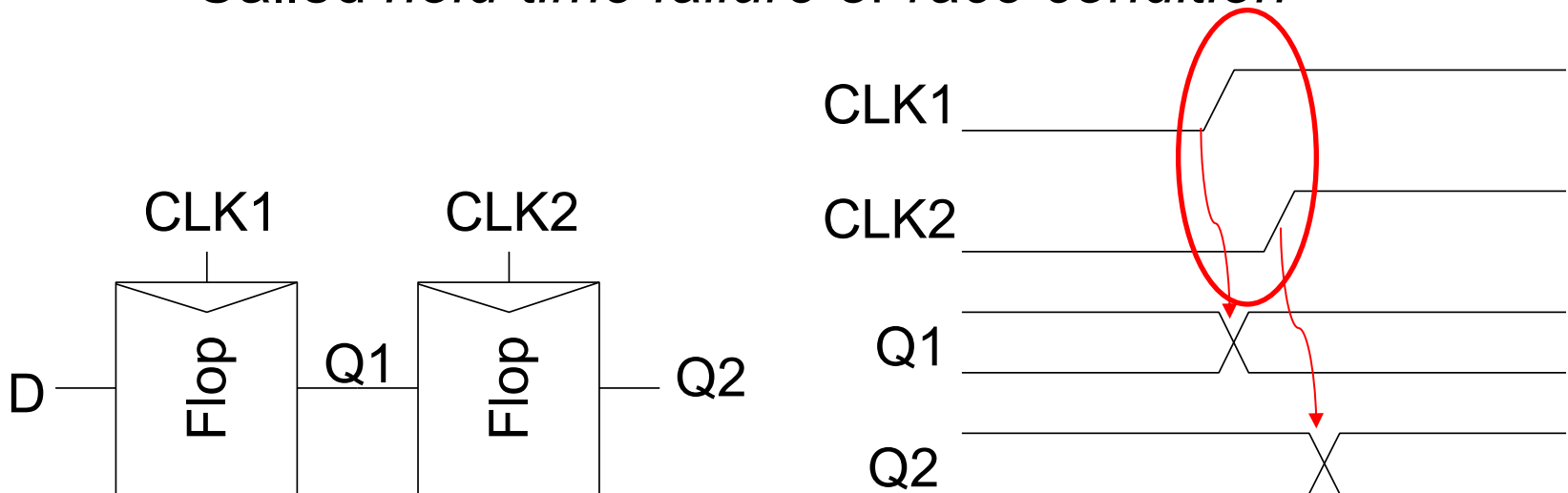
Example: μ Processor Pipeline



MIPS pipeline
example (Wikipedia)

Race Condition

- ❑ Back-to-back flops can malfunction from **clock skew**
 - Second flip-flop fires late
 - Sees first flip-flop change and captures its result
 - Called *hold-time failure* or *race condition*



✗ Token passes through two stages in one clock cycle

Nonoverlapping Clocks

- ❑ Nonoverlapping clocks can prevent races
 - As long as nonoverlap exceeds clock skew
 - Allows for safer but slower design

